



## PAM2322AGEAR

#### **DUAL HIGH-EFFICIENCY PWM STEP-DOWN DC-DC CONVERTER**

### **Description**

The PAM2322AGEAR is a dual step-down current-mode, DC-DC converter. At heavy load, the constant-frequency PWM control performs with excellent stability and transient response. To ensure the longest battery life in portable applications, the PAM2322AGEAR provides a power-saving Pulse-Skipping Modulation (PSM) mode to reduce quiescent current under light load operation

The PAM2322AGEAR supports a range of input voltages from 2.7V to 5.5V, allowing the use of a single Li+/Li-polymer cell, multiple Alkaline/NiMH cell, USB, and other standard power sources. Output 1 is a 1.8V fixed output. Output 2 is adjustable from 0.9V to VIN. Both outputs employ an internal power switch and synchronous rectifier to minimize external part count and realize high efficiency.

Output 1 delivers up to 1000mA output current while output 2 delivers up to 2000mA. Each regulator has an independent enable pin.

Each output of the PAM2322AGEAR can be disabled when a logic low is applied to the channel enable pin. During shutdown, the input is disconnected from the output and the shutdown current is less than  $0.1\mu A$ 

Other key features include under-voltage lockout, soft-start, hiccup mode short circuit protection and thermal shutdown.

### **Features**

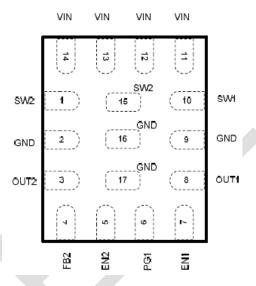
- Supply Voltage:2.7V to 5.5V
- Output Current:

OUT1: 1000mA/Buck, 1.8V Fixed Output

OUT2: 2000mA/Buck

- Switching Frequency:1.2MHz
- Internal Synchronous Rectifier
- Fast Transient Response
- Fast Turn On and Turn Off
- Internal Soft Start
- Internal Compensation
- 100% Duty Cycle Operation
- Power Good Indicator for OUT1
- Under-Voltage Lockout
- Hiccup Mode Short Circuit Protection
- Thermal Shutdown
- Small W-FLGA2520-17 Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Pin Assignments**



W-FLGA2520-17

### **Applications**

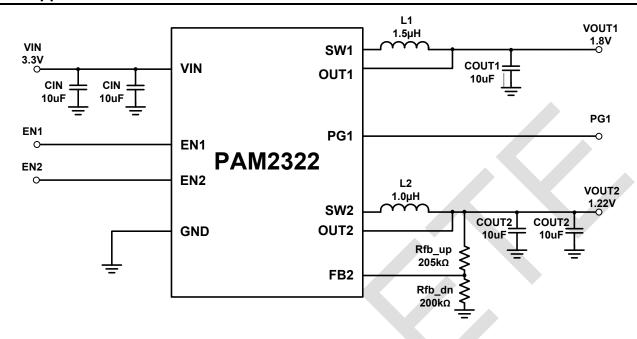
- Portable Electronics
- Personal Information Appliances
- Wireless and DSL Modems

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



## **Typical Applications Circuit**

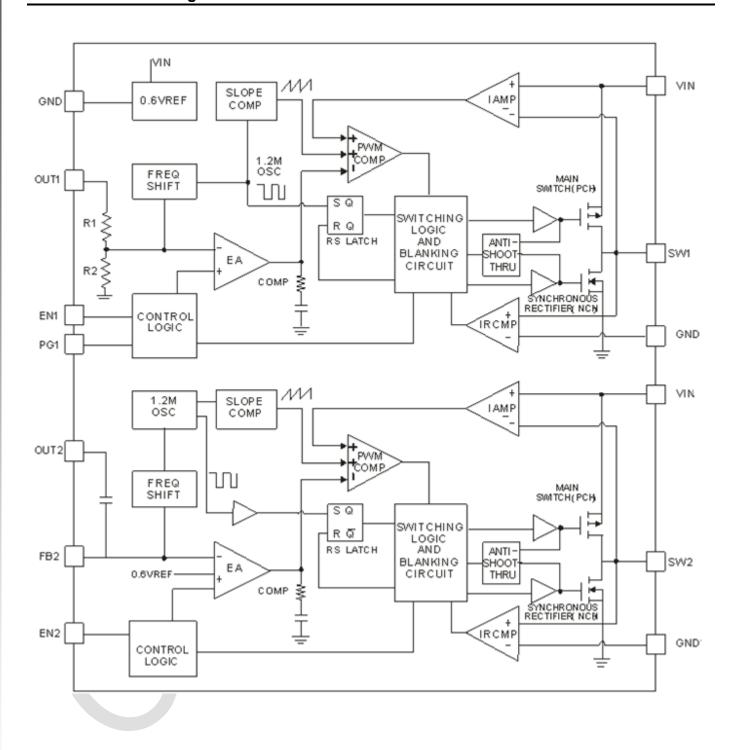


## **Pin Descriptions**

| W-FLGA2520-17  | Name | Function  |  |
|----------------|------|---|--|
| 1, 15          | SW2  | Switch PIN for Output 2, PIN 1 and 15 can be connected on the PCB       |  |
| 2, 9, 16, 17   | GND  | Ground pin, PIN 2, 9, 16, 17 can be connected on the PCB                |  |
| 3              | OUT2 | Output sense pin of Output 2  |  |
| 4              | FB2  | Feedback pin for Output 2, the reference is set internally to 0.6V      |  |
| 5              | EN2  | Enable for Output 2. Pull high to enable channel 2. Pull low to disable |  |
| 6              | PG1  | Output 1 power good indicator pin, open drain output                    |  |
| 7              | EN1  | Enable for Output 1. Pull high to enable channel 1. Pull low to disable |  |
| 8              | OUT1 | Output pin of Output 1, Channel one is internally fixed to 1.8V         |  |
| 10             | SW1  | Switch Pin for Output 1   |  |
| 11, 12, 13, 14 | VIN  | Input voltage pin. PIN 11, 12, 13, 14 can be connected on the PCB       |  |



### **Functional Block Diagram**





### **Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.) (Note 4)

| Parameter                   | Rating                         | Unit |
|-----------------------------|--------------------------------|------|
| Input Voltage               | -0.3 to +6.0                   | V    |
| EN1, EN2, FB2               | -0.3 to V <sub>IN</sub>        | V    |
| SW1 and SW2                 | -0.3 to (V <sub>IN</sub> +0.3) | V    |
| Junction Temperature        | 150                            | °C   |
| Storage Temperature Range   | -65 to +150                    | °C   |
| Soldering Temperature       | 260,10sec                      | °C   |
| ESD Susceptibility (Note 5) |                                |      |
| Human Body Model (HBM)      | 1.5                            | kV   |
| Machine Model (MM)          | 150                            | V    |

Notes: 4. Stresses greater than the 'Absolute Maximum Ratings' specified above may cause permanent damage to the device. These are stress ratings only; functional operation of the device at these or any other conditions exceeding those indicated in this specification is not implied. Device reliability may be affected by exposure to absolute maximum rating conditions for extended periods of time.

5. Semiconductor devices are ESD sensitive and may be damaged by exposure to ESD events. Suitable ESD precautions should be taken when handling and transporting these devices.

### Recommended Operating Conditions (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Parameter                  | Rating      | Unit |
|----------------------------|-------------|------|
| Supply Voltage             | 2.7 to 5.5  | V    |
| Ambient Temperature Range  | -40 to +85  | 2°   |
| Junction Temperature Range | -40 to +125 | C    |

### **Thermal Information**

| Parameter                                | Package       | Symbol | Maximum | Unit |
|--|---------------|--------|---------|------|
| Thermal Resistance (Junction to Case)    | W-FLGA2520-17 | θЈС    | 16      |      |
| Thermal Resistance (Junction to Ambient) | W-FLGA2520-17 | θЈА    | 80      | °C/W |



## $\textbf{Electrical Characteristics} \ (T_A = +25^{\circ}\text{C}, \text{VIN=3.3V}, \text{OUT1=1.8V}, \text{L1=1.5}\mu\text{H}, \text{OUT2=1.2V}, \text{L2=1.0}\mu\text{H}, \text{unless otherwise noted.})$

| PARAMETER                           | SYMBOL              | Test Co                            | nditions                 | MIN   | TYP   | MAX   | UNITS |
|-------------------------------------|---------------------|------------------------------------|--------------------------|-------|-------|-------|-------|
| Input Voltage Range                 | V <sub>IN</sub>     | _                                  |                          | 2.7   | 3.3   | 5.5   | V     |
| LIVII O Threehold                   | .,,                 | V <sub>IN</sub> Rising             |                          | 2.35  | 2.5   | 2.65  | V     |
| UVLO Threshold                      | V <sub>UVLO</sub>   | Hysteresis                         |                          | _     | 400   | _     | mV    |
| Output1 Voltage Accuracy            | OUT1                | -                                  | _                        | -4    |       | +4    | %     |
| OUT2 Feedback Voltage               | $V_{FB2}$           | No Load                            |                          | 0.591 | 0.60  | 0.609 | V     |
| Output2 Voltage Accuracy            | OUT2                | VIN 3.0 to 3.6V, T resistors 0.25% | A 0-70°C, VFB            | -2.7  | -     | 2.7   | %     |
| Current Limit                       |                     | Output 1                           |                          |       | 1.5   | _     | Α     |
| Current Limit                       | I <sub>LIM</sub>    | Output 2                           |                          |       | 3     |       | Α     |
| Quiescent Current                   | ΙQ                  | No load                            |                          | _     | 60    | 100   | μA    |
| Shutdown Current                    | I <sub>SD</sub>     | V <sub>EN</sub> = 0V               |                          | _     |       | 0.1   | μA    |
| SW Leakage Current                  | I <sub>LSW</sub>    | V <sub>EN</sub> = 0V               |                          | _     |       | 1     | μA    |
| Oscillator Frequency                | f <sub>OSC</sub>    | -                                  | -                        | 1.0   | 1.2   | 1.4   | MHz   |
|                                     |                     | I <sub>DS</sub> =100mA             | P MOSFET                 |       | 120   | _     | mΩ    |
| Danier Occurs On Otata Basistana    |                     | Output 1                           | N MOSFET                 | _     | 80    | _     | mΩ    |
| Drain-Source On-State Resistance    | R <sub>DS(ON)</sub> | IDS TOUTIA                         | P MOSFET                 | _     | 50    | _     | mΩ    |
|                                     |                     |                                    | N MOSFET                 | _     | 40    | _     | mΩ    |
| :                                   | _                   | VIN = 0 to 3.3V,lo=200mA           |                          | _     | _     | 1000  | μs    |
| Turn-on Time                        | Turn-on Time Ts EN  |                                    | EN = 0 to 3.3V, Io=200mA |       | _     | 300   | μs    |
| Turn-off Time                       | Toff                | EN = 3.3 to 0V, lo                 | =5mA                     | _     | _     | 7000  | μs    |
| Turn-on Pre-charge Time             | Tchg                | EN = 0 to 3.3V, lo<br>to 1.2V      |                          | _     | _     | 300   | μs    |
| Turn-off Discharge Time             | Tdis                | EN = 3.3 to 0V, lo<br>1.1V         | =5mA Vo=1.2V to          | _     | _     | 450   | μs    |
| High Impedance Delay                | OUT1, SW1           | EN1 transitions high to low        |                          | _     | _     | 10    |       |
| Tright impossance Botal             | OUT2, SW2,<br>FB2   | EN2 transitions high to low        |                          | _     | _     | 10    | μs    |
| EN1/EN2 Threshold High              | V <sub>EH</sub>     | _                                  |                          | 1.2   | _     | _     | V     |
| EN1/EN2 Threshold Low               | V <sub>EL</sub>     | _                                  |                          | _     | _     | 0.4   | V     |
| Over Temperature Protection         | OTP                 | _                                  |                          |       | 150   | _     | °C    |
| OTP Hysteresis                      | ОТН                 | _                                  |                          |       | 30    | _     | °C    |
| PG Pin Trigger Delay                | _                   | _                                  |                          | _     | 90    | _     | us    |
| PG Pin Threshold (Relative to Vout) | _                   | _                                  |                          | _     | +/-10 | _     | %     |
| PG Open Drain Impedance (PG=PVin)   | _                   |                                    | _                        | _     | 500K  | _     | Ω     |
| PG Open Drain Impedance (PG=low)    | _                   | _                                  |                          | _     | _     | 100   | Ω     |



#### Electrical Characteristics (T<sub>A</sub>= +25°C, VIN=3.3V, OUT1=1.8V, L1=1.5μH, OUT2=1.2V,L2=1.0μH, unless otherwise noted.) (cont.)

| PARAMETER        | SYMBOL    | Test Conditions        | MIN      | TYP   | MAX | UNITS |
|------------------|-----------|------------------------|----------|-------|-----|-------|
| PSM Threshold    | ITH       | OUT1                   | _        | 100   | _   | mA    |
| PSIVI TITIESHOID | 117       | OUT2                   | _        | 200   | _   | mA    |
| PSM Hysteresis   | IHY       | OUT1                   | _        | 6     | _   | mA    |
| FSIVI HYSIEIESIS | Int       | OUT2                   | _        | 20    | _   | mA    |
|                  |           | IOUT1= 300uA to 600uA  | _        | 55    | _   | %     |
|                  | EffiOUT1  | IOUT1= 10mA            | _        | 82    |     | %     |
| Efficiency       |           | IOUT1= 300mA to 400mA  | _        | 92    |     | %     |
| Efficiency       | EffiOUT2  | IOUT2= 200uA to 300uA  |          | 50    |     | %     |
|                  |           | IOUT2= 10mA            | -        | 80    |     | %     |
|                  |           | IOUT2= 900mA to 1200mA |          | 90    |     | %     |
| Load Degulation  | VLDR-OUT1 | IOUT1= 100mA to 500mA  | _        | 0.05% |     | VO/mA |
| Load Regulation  | VLDR-OUT2 | IOUT2= 200mA to 1500mA | _        | 0.05% | _   | VO/mA |
| Line Degulation  | VLNR-OUT1 | VIN= 3.0V to 3.6V      | <b>—</b> | 0.1%  | —   | VO/V  |
| Line Regulation  | VLNR-OUT2 | VIN= 3.0V to 3.6V      |          | 0.1%  | —   | VO/V  |

### **Application Information**

The typical application circuit of PAM2322AGEAR is shown on page 2. External component selection is determined by the load requirement, selecting inductors L1 and L2 first and then input capacitor CIN and output capacitor COUT.

### Inductor selection

For most applications, the value of the inductor is in the range of  $1\mu$ H to  $3.3\mu$ H, which is chosen based on the desired current ripple. Large value inductor brings lower current ripple and small value inductor results in higher current ripple. Higher  $V_{IN}$  and  $V_{OUT}$  increase the current ripple as well shown in the following equation. For OUT1 with 1A loading current requirement, the reasonable current ripple starting point f is  $\Delta$ IL = 0.4A (40% of 1A), For OUT2 with 2A loading current requirement, the reasonable current ripple starting point is  $\Delta$ IL = 0.8A (40% of 2A)

$$\Delta I_{L} = \frac{1}{(f)(L)} Vout \left(1 - \frac{Vout}{Vin}\right)$$

The DC current rating of the inductor should be at least equal to the maximum load current plus half of the current ripple to prevent core saturation. A low DC-resistance inductor is better to get higher efficiency.

#### **CIN and COUT selection**

To prevent input large voltage transient, a low ESR capacitor with the maximum RMS current must be used. The maximum capacitor RMS current is given by:

$$C_{\text{IN}} \text{requiredI}_{\text{RMS}} \cong I_{\text{OMAX}} \frac{\left[V_{\text{OUT}} \left(V_{\text{IN}} - V_{\text{OUT}}\right)\right]^{\frac{1}{2}}}{V_{\text{IN}}}$$

This formula shows that I<sub>RMS</sub> has the maximum value at VIN =2VOUT, where IRMS = IOUT/2 and this worst-case is common used for design.



### **Application Information (cont.)**

#### CIN and COUT selection (cont.)

The selection of Cout is driven by the requirement of effective series resistance (ESR) and the output voltage ripple ΔVOUT is determined by:

$$\Delta V_{\text{OUT}} \approx \Delta I_{\text{L}} \left( \text{ESR} + \frac{1}{8} \text{fC}_{\text{OUT}} \right)$$

Where f is the operating frequency, COUT is output capacitance and AIL is rippling current flowing through the inductor.

When output voltage is set, the output voltage ripple changes with the input voltage and is at its worst when input voltage reaches a high level.

#### **Using Ceramic Input and Output Capacitors**

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. Using ceramic capacitors can achieve very low output ripple and small PCB size. X5R or X7R are preferred, because they have the better temperature and voltage characteristics.

#### **Output Voltage Setting**

PAM2322AGEAR output1 is fixed at 1.8V and cannot be adjusted. For other voltage options contact your Diodes representative.

Output2 can be adjusted based on an external connected voltage divider. The internal reference of FB2 is 0.6V (Typical). The output voltage can be found based on the following calculation. The general output voltage is given in Table 1.

$$V_{\text{OUT2}} = 0.6 \times \left(1 + \frac{R_{\text{FB\_UP}}}{R_{\text{FB\_LOW}}}\right)$$

Table 1: Resistor Selection for Output 2 Voltage Setting

| VOUT2 | Rfb_up | Rfb_low |
|-------|--------|---------|
| 1.22V | 205k   | 200k    |
| 1.5V  | 150k   | 100k    |
| 1.8V  | 300k   | 150k    |
| 2.5V  | 380k   | 120k    |
| 3.3V  | 680k   | 150k    |

#### Pulse Skipping Mode (PSM) Description

When load current decreases, the peak switch current from Power-PMOS is lower than skipping current threshold and the device will enter Pulse Skipping Mode. In this mode, the device has two states, working state and idle state. Firstly, the device enters working state controlled by internal error amplifier. When the feedback voltage gets higher than internal reference voltage, the device will enter idle state with internal blocks disabled. When the feedback voltage gets lower than the internal reference voltage, the convertor will enter the working state again.

#### **UVLO and Soft-Start**

The reference and the circuit remain reset until the VIN crosses its UVLO threshold. The PAM2322AGEAR has an internal soft-start circuit that limits the in-rush current during start-up. This prevents possible voltage drops of the input voltage and eliminates an output voltage overshoot.



### **Application Information (cont.)**

### **Hiccup Mode Short Circuit Control**

When the converter output1 or output2 is shorted, or the device is overloaded during high-side MOSFET current-limit triggering, it will turn off the high-side MOSFET and turn on the low-side MOSFET. An internal counter is used to count the number of the current-limit triggering. The counter is reset when consecutive high-side MOSFET turn on without reaching current limit. If the current-limit condition persists, the counter fills up. The control logic then stops both high side and low side MOSFETs and waits for a hiccup period, before attempting a new soft-start sequence. The counter bit is decided by  $V_{FB}$  voltage. If  $V_{FB}$  voltage. If  $V_{FB}$  voltage. If  $V_{FB}$  voltage. If  $V_{FB}$  is 3-bit counter; If  $V_{FB}$  >0.2V it is 6-bit counter. The typical hiccup mode duty cycle is 1.7%. The hiccup mode is disabled during soft-start time.

#### **Over Temperature Protection**

The internal thermal temperature protection circuitry is provided to protect the integrated circuit in the event that the maximum junction temperature is exceeded. When the junction temperature exceeds +150°C, it shuts down the internal control circuit and switching power MOSFET. The PAM2322AGEAR will restart automatically under the control of soft-start circuit when the junction temperature decreases to +120°C.

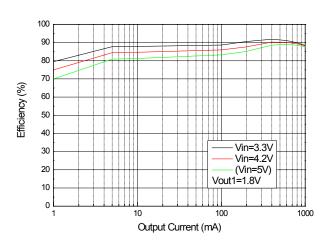
#### **Power Good Flag**

PG1 pin is power good indicator. The output of this pin is an open drain with internal pull up resistor to VIN. PG is pulled up to VIN when the output1 voltage (1.8V) is within 10% of the regulation level, otherwise it is low.

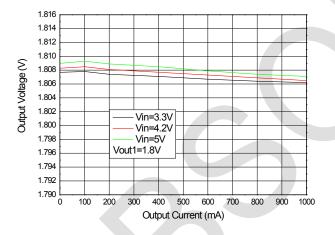


## Typical Performance Characteristics (TA= +25°C, VIN=3.3V, OUT1=1.8V, L=1.5µH, OUT2=1.2V,L=1.0µH, unless otherwise noted.)

#### OUT1 Efficiency vs. Output Current

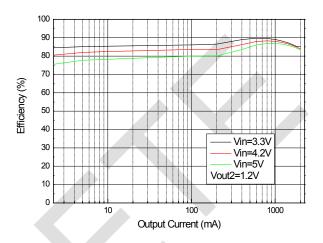


OUT1 Output Voltage vs. Output Current

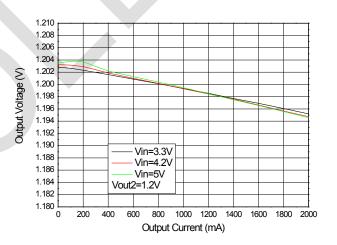


OUT1 Line Regulation vs. Input Voltage

#### OUT2 Efficiency vs. Output Current



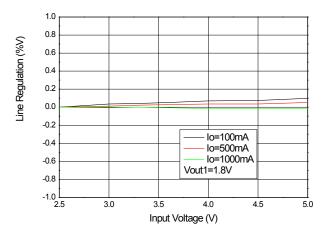
OUT2 Output Voltage vs. Output Current

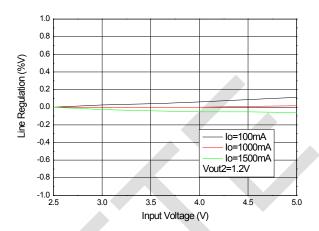


OUT2 Line Regulation vs. Input Voltage

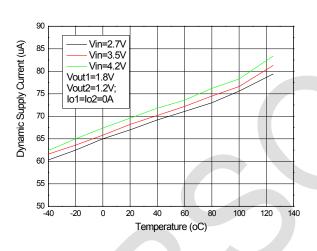


## Typical Performance Characteristics (TA= +25°C, VIN=3.3V, OUT1=1.8V, L=1.5µH, OUT2=1.2V,L=1.0µH, unless otherwise noted.)

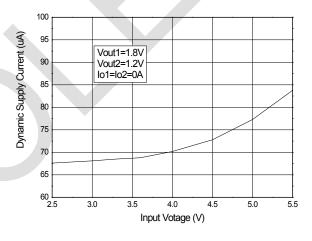




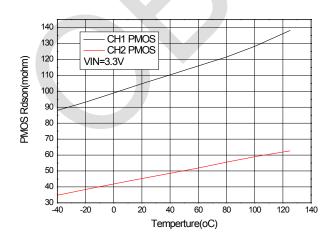
Dynamic Supply Current vs. Temperature



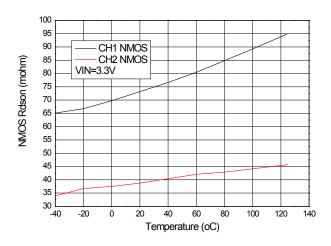
Dynamic Supply Current vs. Input Current



PMOS Rdson vs. Temperature

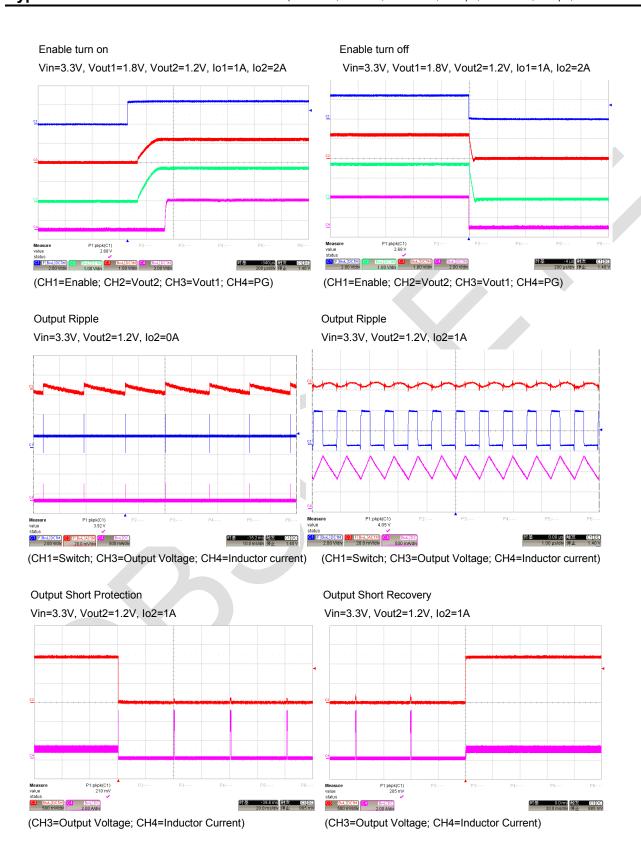


NMOS Rdson vs. Temperature



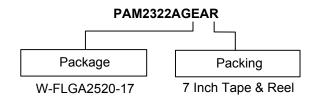


## Typical Performance Characteristics (TA= +25°C, VIN=3.3V, OUT1=1.8V, L=1.5µH, OUT2=1.2V,L=1.0µH, unless otherwise noted.)





### **Ordering Information**



| Part Number  | Marking    | Package Type  | Standard Package        |
|--------------|------------|---------------|-------------------------|
| PAM2322AGEAR | CRA<br>XYW | W-FLGA2520-17 | 3,000 Units/Tape & Reel |

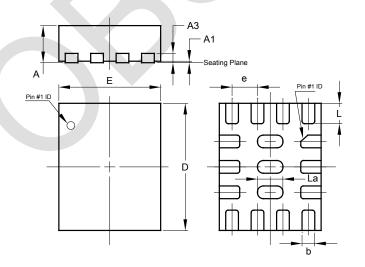
# **Marking Information**

CRV XYW CR: Product Code of PAM2322 V: Output Voltage X: Internal Code

Y: Year W: Week

## Package Outline Dimensions (All dimensions in mm.)

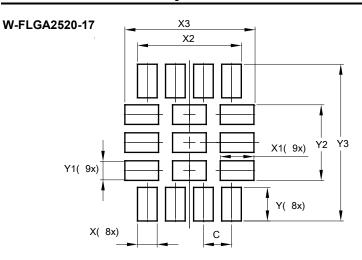
### W-FLGA2520-17



| W-FLGA2520-17        |             |       |  |  |
|----------------------|-------------|-------|--|--|
| Dim                  | Min         | Max   |  |  |
| Α                    | 0.700       | 0.800 |  |  |
| A1                   | 0           | 0.050 |  |  |
| A3                   | 0.0203REF   |       |  |  |
| b                    | 0.200       | 0.300 |  |  |
| D                    | 2.420       | 2.580 |  |  |
| Е                    | 1.950 2.050 |       |  |  |
| е                    | 0.500TYP    |       |  |  |
| L                    | 0.320       | 0.480 |  |  |
| La                   | 0.424       | 0.576 |  |  |
| All Dimensions in mm |             |       |  |  |



# **Recommended Pad Layout**



| Dimensions | Value<br>(in mm) |
|------------|------------------|
| С          | 0.500            |
| X          | 0.350            |
| X1         | 0.600            |
| X2         | 1.850            |
| Х3         | 2.320            |
| Y          | 0.600            |
| Y1         | 0.350            |
| Y2         | 1.350            |
| Y3         | 2.800            |



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